



520.34403CV4

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): T. MASUDA, et al

Serial No.: 09/421,043

Filed: October 20, 1999

For: PLASMA ETCHING APPARATUS AND PLASMA ETCHING METHOD

Group: 1763

Examiner: A. Mulero

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10/9/02
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AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

October 4, 2002

Sir:

The following amendments and remarks are respectfully submitted in connection with the above-identified application in response to the Office Action dated June 4, 2002.

IN THE SPECIFICATION:

Page 21, please amend the paragraph beginning at line 6 as follows:

E' The plasma etching apparatus in this embodiment is structured as mentioned above and each unit in the reactor, particular the inner surface of the side wall 102 and the ring 116, and temperature control of the sample holder ring 132 and deposition control of reaction products will be explained in detail hereunder.

IN THE CLAIMS:

Please amend claims 21-24 as follows:

21. (twice amended) A plasma etching apparatus for etching of a sample

E2 comprising:

10/07/2002 TBESHAH1 00000064 09421043

01 FC:103
02 FC:102

180.00 OP
84.00 OP